

32,768-WORD BY 8-BIT STATIC RAM

DESCRIPTION

The TC55257DPL/DFL/DFTL/DTRL is a 262,144-bit static random access memory (SRAM) organized as 32,768 words by 8 bits. Fabricated using Toshiba's CMOS Silicon gate process technology, this device operates from a single 2.7 to 5.5 V power supply. Advanced circuit technology provides both high speed and low power at an operating current of 5 mA/MHz (typ) and a minimum cycle time of 55 ns. It is automatically placed in low-power mode at 0.3 μ A standby current (typ) when chip enable (\overline{CE}) is asserted high. There are two control inputs. \overline{CE} is used to select the device and for data retention control, and output enable (\overline{OE}) provides fast memory access. This device is well suited to various microprocessor system applications where high speed, low power and battery backup are required. The TC55257DPL/DFL/DFTL/DTRL is available in a standard plastic 28-pin dual-in-line package (DIP), plastic 28-pin small-outline package (SOP) and normal and reverse pinout plastic 28-pin thin-small-outline package (TSOP).

FEATURES

- Low-power dissipation
Operating: 27.5 mW/MHz (typical)
- Standby current of 2 μ A (maximum) at $T_a = 25^\circ\text{C}$
- Single power supply voltage of 2.7 to 5.5 V
- Power down features using \overline{CE} .
- Data retention supply voltage of 2 to 5.5 V
- Direct TTL compatibility for all inputs and outputs

- Access Times (maximum):

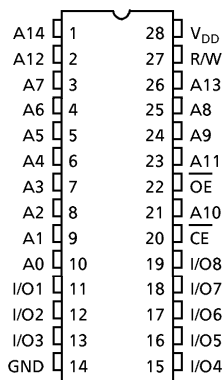
	5 V \pm 10%			2.7 to 5.5 V	
	-55V	-70V	-85V	-55V/-70V	-85V
Access Time	55 ns	70 ns	85 ns	120 ns	150 ns
\overline{CE} Access Time	55 ns	70 ns	85 ns	120 ns	150 ns
\overline{OE} Access Time	30 ns	35 ns	45 ns	70 ns	75 ns

- Packages:

DIP28-P-600-2.54 (DPL) (Weight: 4.42 g typ)
 SOP28-P-450-1.27 (DFL) (Weight: 0.79 g typ)
 TSOP I 28-P-0.55 (DFTL) (Weight: 0.22 g typ)
 TSOP I 28-P-0.55A (DTRL) (Weight: 0.22 g typ)

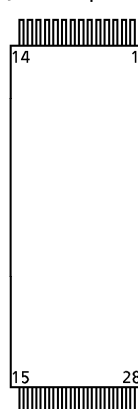
PIN ASSIGNMENT (TOP VIEW)

28 PIN DIP & SOP

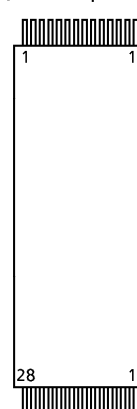


28 PIN TSOP

(Normal pinout)



(Reverse pinout)



PIN NAMES

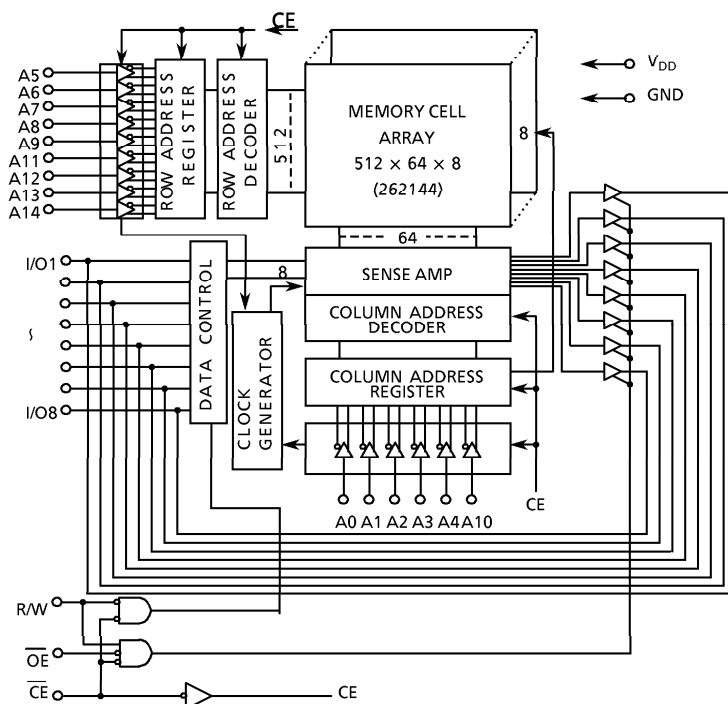
A0 to A14	Address Inputs
R/W	Read/Write Control
\overline{OE}	Output Enable
\overline{CE}	Chip Enable
I/O1 to I/O8	Data Input/Output
V_{DD}	Power
GND	Ground

PIN NO.	1	2	3	4	5	6	7	8	9	10	11	12	13	14
PIN NAME	\overline{OE}	A ₁₁	A ₉	A ₈	A ₁₃	R/W	V_{DD}	A ₁₄	A ₁₂	A ₇	A ₆	A ₅	A ₄	A ₃
PIN NO.	15	16	17	18	19	20	21	22	23	24	25	26	27	28
PIN NAME	A ₂	A ₁	A ₀	I/O1	I/O2	I/O3	GND	I/O4	I/O5	I/O6	I/O7	I/O8	\overline{CE}	A ₁₀

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BLOCK DIAGRAM



OPERATION MODE

MODE	$\overline{\text{CE}}$	$\overline{\text{OE}}$	R/W	I/O1 to I/O8	POWER
Read	L	L	H	D _{OUT}	I _{DDO}
Write	L	X	L	D _{IN}	I _{DDO}
Outputs Disabled	L	H	H	High-Z	I _{DDO}
Standby	H	X	X	High-Z	I _{DDS}

Note: x = don't care. H = logic high. L = logic low.

ABSOLUTE MAXIMUM RATINGS

SYMBOL	RATING	VALUE	UNIT
V _{DD}	Power Supply Voltage	– 0.3 to 7.0	V
V _{IN}	Input Voltage	– 0.3* to 7.0	V
V _{I/O}	Input/Output Voltage	– 0.5* to V _{DD} + 0.5	V
P _D	Power Dissipation	1.0/0.6 **	W
T _{solder}	Soldering Temperature (10 s)	260	°C
T _{strg}	Storage Temperature	– 55 to 150	°C
T _{opr}	Operating Temperature	0 to 70	°C

* – 3.0 V when measured at a pulse width of 50 ns

**** SOP**

DC RECOMMENDED OPERATING CONDITIONS ($T_a = 0^\circ \text{ to } 70^\circ \text{C}$)

SYMBOL	PARAMETER	5 V \pm 10%			2.7 to 5.5 V			UNIT
		MIN	TYP	MAX	MIN	TYP	MAX	
V_{DD}	Power Supply Voltage	4.5	–	5.5	2.7	–	5.5	V
V_{IH}	Input High Voltage	2.2	–	$V_{DD} + 0.3$	$V_{DD} - 0.2$	–	$V_{DD} + 0.3$	
V_{IL}	Input Low Voltage	-0.3^*	–	0.8	-0.3^*	–	0.2	
V_{DH}	Data Retention Supply Voltage	2.0	–	5.5	2.0	–	5.5	

* – 3.0 V when measured at a pulse width of 50 ns

DC CHARACTERISTICS ($T_a = 0^\circ \text{ to } 70^\circ \text{C}$, $V_{DD} = 3 \text{ V} \pm 10\%$)

SYMBOL	PARAMETER	TEST CONDITION		MIN	TYP	MAX	UNIT
I _{IL}	Input Leakage Current	V _{IN} = 0 V to V _{DD}		–	–	± 1.0	μA
I _{OH}	Output High Current	V _{OH} = 2.4 V		– 1.0	–	–	mA
I _{OL}	Output Low Current	V _{OL} = 0.4 V		4.0	–	–	mA
I _{LO}	Output Leakage Current	$\overline{CE} = V_{IH}$ or R/W = V _{IL} or $\overline{OE} = V_{IH}$ V _{OUT} = 0 V to V _{DD}		–	–	± 1.0	μA
I _{DDO1}	Operating Current	$\overline{CE} = V_{IL}$ R/W = V _{IH} Other Inputs = V _{IH} /V _{IL} I _{OUT} = 0 mA	t _{cycle} = 1 μs	–	10	–	mA
			t _{cycle} = min	–	–	70	
I _{DDO2}		$\overline{CE} = 0.2 \text{ V}$ R/W = V _{DD} – 0.2 V Other Inputs = V _{DD} – 0.2 V/0.2 V I _{OUT} = 0 mA	t _{cycle} = 1 μs	–	5	–	mA
			t _{cycle} = min	–	–	60	
I _{DDS1}	Standby Current	$\overline{CE} = V_{IH}$		–	–	3	mA
I _{DDS2}	Standby Current	$\overline{CE} = V_{DD} - 0.2 \text{ V}$	Ta = 0° to 70°C	–	–	20	μA
		V _{DD} = 2.0 to 5.5 V	Ta = 25°C	–	0.3	2	μA

DC CHARACTERISTICS ($T_a = 0^\circ \text{ to } 70^\circ \text{C}$, $V_{DD} = 5 \text{ V} \pm 10\%$)

SYMBOL	PARAMETER	TEST CONDITION			MIN	TYP	MAX	UNIT
I _{IL}	Input Leakage Current	V _{IN} = 0 V to V _{DD}			–	–	± 1.0	μA
I _{OH}	Output High Current	V _{OH} = V _{DD} – 0.2 V			– 0.1	–	–	mA
I _{OL}	Output Low Current	V _{OL} = 0.2 V			0.1	–	–	mA
I _{LO}	Output Leakage Current	CE = V _{IH} or R/W = V _{IL} or OE = V _{IH} , V _{OUT} = 0 V to V _{DD}			–	–	± 1.0	μA
I _{DDO2}	Operating Current	CE = 0.2 V R/W = V _{DD} – 0.2 V, I _{OUT} = 0 mA Other Inputs = V _{DD} – 0.2 V/0.2 V	T _{cycle}	min	–	–	20	mA
				1 μs	–	–	5	
I _{DDs2}	Standby Current	CE = V _{DD} – 0.2 V	V _{DD} = 3 V ± 10%	Ta = 25°C	–	1	1.5	μA
				Ta = 0° to 70°C	–	–	15	
			V _{DD} = 3.0 V	Ta = 25°C	–	–	1	
				Ta = 0° to 40°C	–	–	2	
				Ta = 0° to 70°C	–	–	10	

CAPACITANCE ($T_a = 25^\circ \text{C}$, $f = 1 \text{ MHz}$)

SYMBOL	PARAMETER	TEST CONDITION	MAX	UNIT
C_{IN}	Input Capacitance	$V_{IN} = \text{GND}$	10	pF
C_{OUT}	Output Capacitance	$V_{OUT} = \text{GND}$	10	

Note: This parameter is periodically sampled and is not 100% tested.

AC CHARACTERISTICS AND OPERATING CONDITIONS ($T_a = 0^\circ \text{ to } 70^\circ \text{C}$, $V_{DD} = 5 \text{ V} \pm 10\%$)

READ CYCLE

SYMBOL	PARAMETER	TC55257DPL/DFL/DFTL/DTRL						UNIT
		-55V		-70V		-85V		
		MIN	MAX	MIN	MAX	MIN	MAX	
t _{RC}	Read Cycle Time	55	–	70	–	85	–	ns
t _{ACC}	Address Access Time	–	55	–	70	–	85	
t _{CO}	Chip Enable Access Time	–	55	–	70	–	85	
t _{OE}	Output Enable Access Time	–	30	–	35	–	45	
t _{COE}	Chip Enable Low to Output Active	10	–	10	–	10	–	
t _{OEE}	Output Enable Low to Output Active	5	–	5	–	5	–	
t _{OD}	Chip Enable High to Output High-Z	–	20	–	25	–	30	
t _{ODO}	Output Enable High to Output High-Z	–	20	–	25	–	30	
t _{OH}	Output Data Hold Time	10	–	10	–	10	–	

WRITE CYCLE

SYMBOL	PARAMETER	TC55257DPL/DFL/DFTL/DTRL						UNIT
		-55V		-70V		-85V		
		MIN	MAX	MIN	MAX	MIN	MAX	
t _{WC}	Write Cycle Time	55	–	70	–	85	–	ns
t _{WP}	Write Pulse Width	45	–	50	–	60	–	
t _{CW}	Chip Enable to End of Write	50	–	60	–	65	–	
t _{AS}	Address Setup Time	0	–	0	–	0	–	
t _{WR}	Write Recovery Time	0	–	0	–	0	–	
t _{ODW}	R/W Low to Output High-Z	–	20	–	25	–	30	
t _{OEW}	R/W High to Output Active	5	–	5	–	5	–	
t _{DS}	Data Setup Time	25	–	30	–	40	–	
t _{DH}	Data Hold Time	0	–	0	–	0	–	

AC TEST CONDITIONS

Output load: 30 pF + one TTL gate (-55V)

100 pF + one TTL gate (-70L, -85L)

Input pulse level: 0.6 V, 2.4 V

Timing measurements: 1.5 V

Reference level: 1.5 V

 t_R, t_F : 5 ns

AC CHARACTERISTICS AND OPERATING CONDITIONS ($T_a = 0^\circ$ to 70°C , $V_{DD} = 2.7$ to 5.5 V)

READ CYCLE

SYMBOL	PARAMETER	TC55257DPL/DFL/DFTL/DTRL				UNIT
		-55V/-70V		-85V		
		MIN	MAX	MIN	MAX	
t _{RC}	Read Cycle Time	120	–	150	–	ns
t _{ACC}	Address Access Time	–	120	–	150	
t _{CO}	Chip Enable Access Time	–	120	–	150	
t _{OE}	Output Enable Access Time	–	70	–	75	
t _{COE}	Chip Enable Low to Output Active	10	–	10	–	
t _{OEE}	Output Enable Low to Output Active	5	–	5	–	
t _{OD}	Chip Enable High to Output High-Z	–	50	–	50	
t _{ODO}	Output Enable High to Output High-Z	–	50	–	50	
t _{OH}	Output Data Hold Time	10	–	10	–	

WRITE CYCLE

SYMBOL	PARAMETER	TC55257DPL/DFL/DFTL/DTRL				UNIT
		-55V/-70V		-85V		
		MIN	MAX	MIN	MAX	
t _{WC}	Write Cycle Time	120	–	150	–	ns
t _{WP}	Write Pulse Width	80	–	100	–	
t _{CW}	Chip Enable to End of Write	100	–	120	–	
t _{AS}	Address Setup Time	0	–	0	–	
t _{WR}	Write Recovery Time	0	–	0	–	
t _{ODW}	R/W Low to Output High-Z	–	50	–	50	
t _{OEW}	R/W High to Output Active	5	–	5	–	
t _{DS}	Data Setup Time	50	–	60	–	
t _{DH}	Data Hold Time	0	–	0	–	

AC TEST CONDITIONS

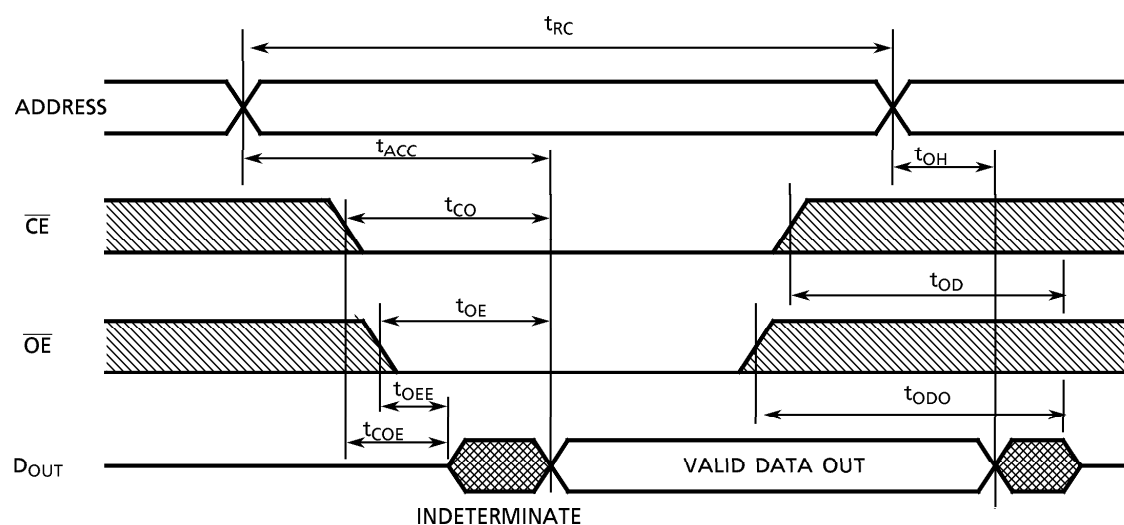
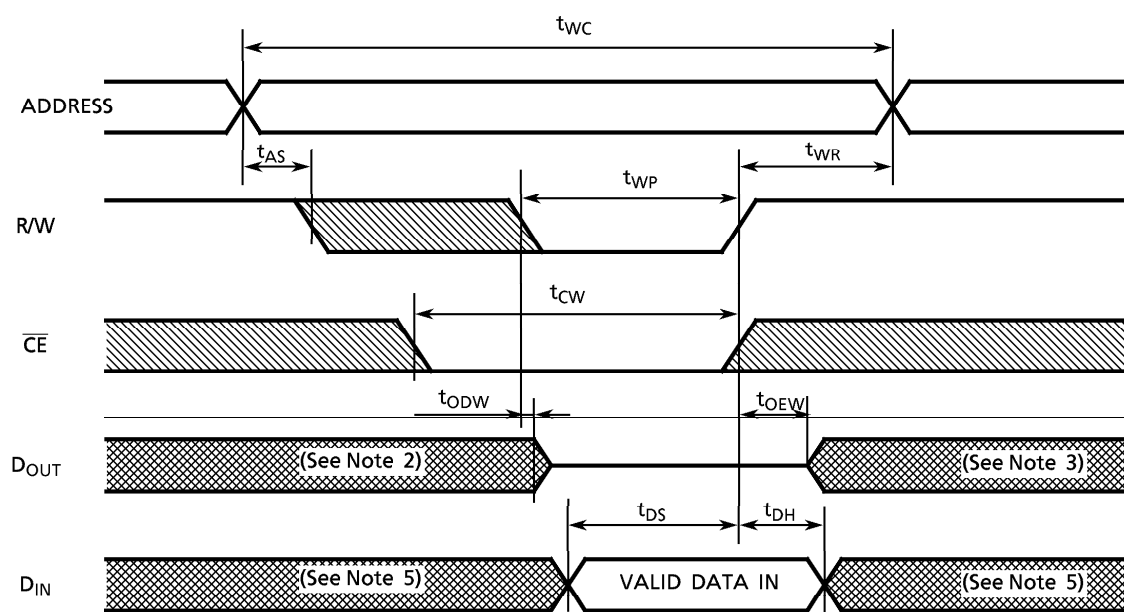
Output load: 100 pF (including jig)

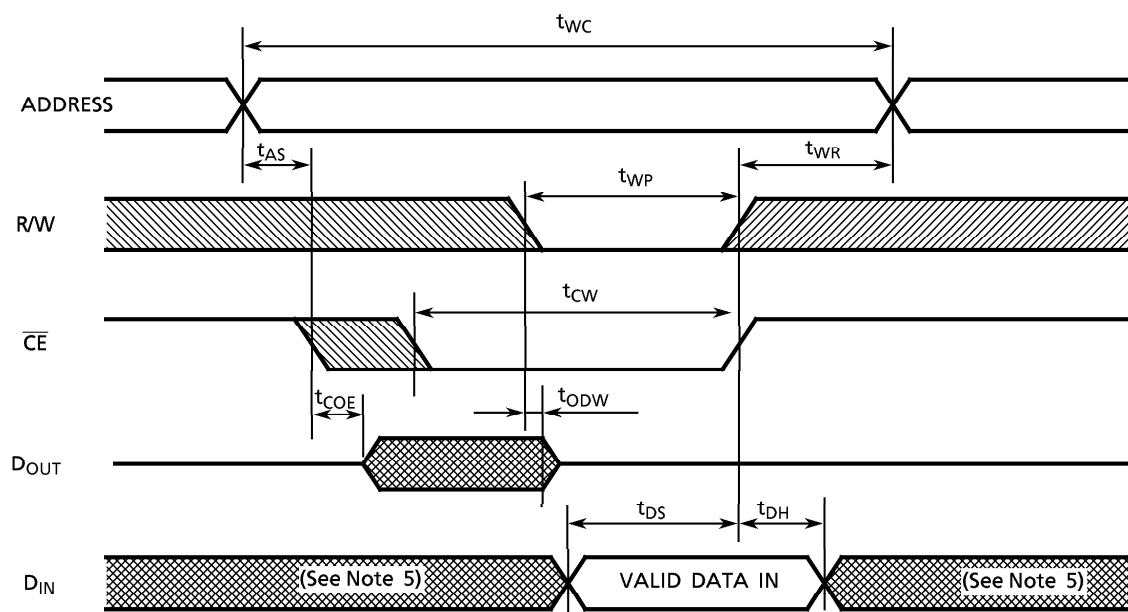
Input pulse level: 0.2 V, $V_{DD} - 0.2\text{ V}$

Timing measurements: 1.5 V

Reference level: 1.5 V

t_R , t_F : 5 ns

TIMING DIAGRAMS
READ CYCLE (See Note 1)

WRITE CYCLE 1 (R/W CONTROLLED) (See Note 4)


WRITE CYCLE 2 (\overline{CE} CONTROLLED) (See Note 4)


Note: (1) R/W remains HIGH for the read cycle.

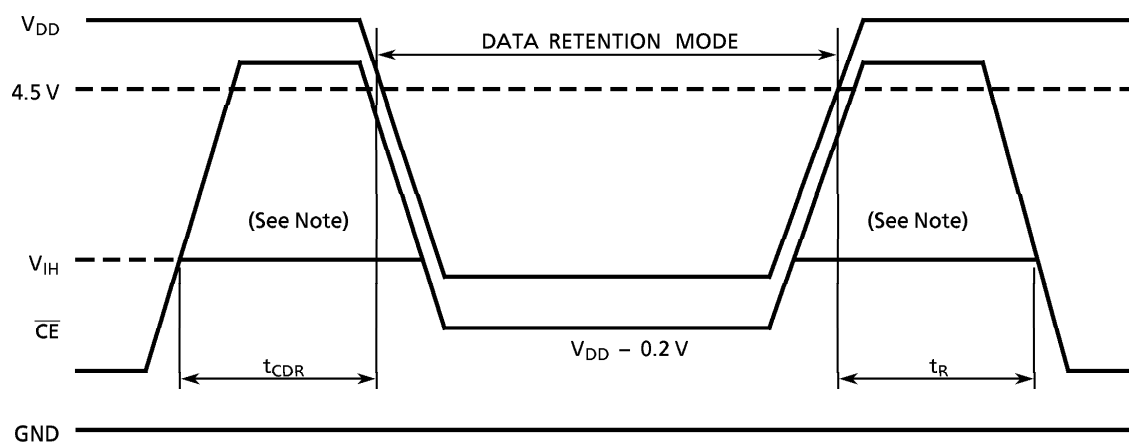
- (2) If \overline{CE} goes LOW coincident with or after R/W goes LOW, the outputs will remain at high impedance.
- (3) If \overline{CE} goes HIGH coincident with or before R/W goes HIGH, the outputs will remain at high impedance.
- (4) If \overline{OE} is HIGH during the write cycle, the outputs will remain at high impedance.
- (5) Because I/O signals may be in the output state at this time, input signals of reverse polarity must not be applied.

DATA RETENTION CHARACTERISTICS ($T_a = 0^\circ$ to 70°C)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNIT
V_{DH}	Data Retention Supply Voltage	2.0	—	5.5	V
I_{DDS2}	Standby Current	$V_{DH} = 3.0\text{ V}$	—	10*	μA
		$V_{DH} = 5.5\text{ V}$	—	20	
t_{CDR}	Chip Deselect to Data Retention Mode Time	0	—	—	ns
t_R	Recovery Time	t_{RC} (See Note)	—	—	

* $2\text{ }\mu\text{A}$ (max) at $T_a = 0^\circ$ to 40°C

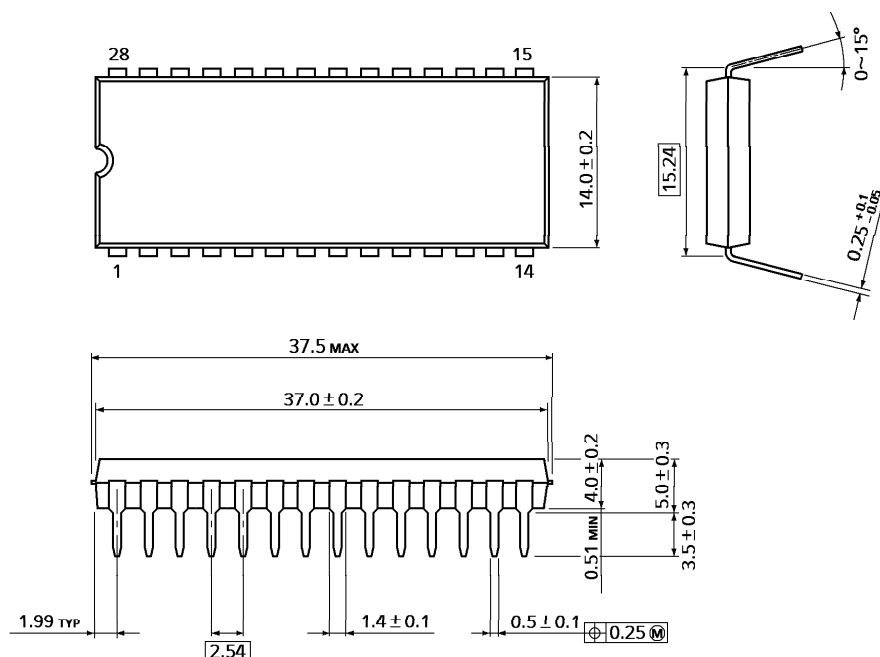
Note: Read cycle time.

CE CONTROLLED DATA RETENTION MODE


Note: When \overline{CE} is operating at the V_{IH} level (2.2 V), the standby current is given by I_{DDS1} during the transition of V_{DD} from 4.5 to 2.4 V.

PACKAGE DIMENSIONS (DIP28-P-600-2.54)

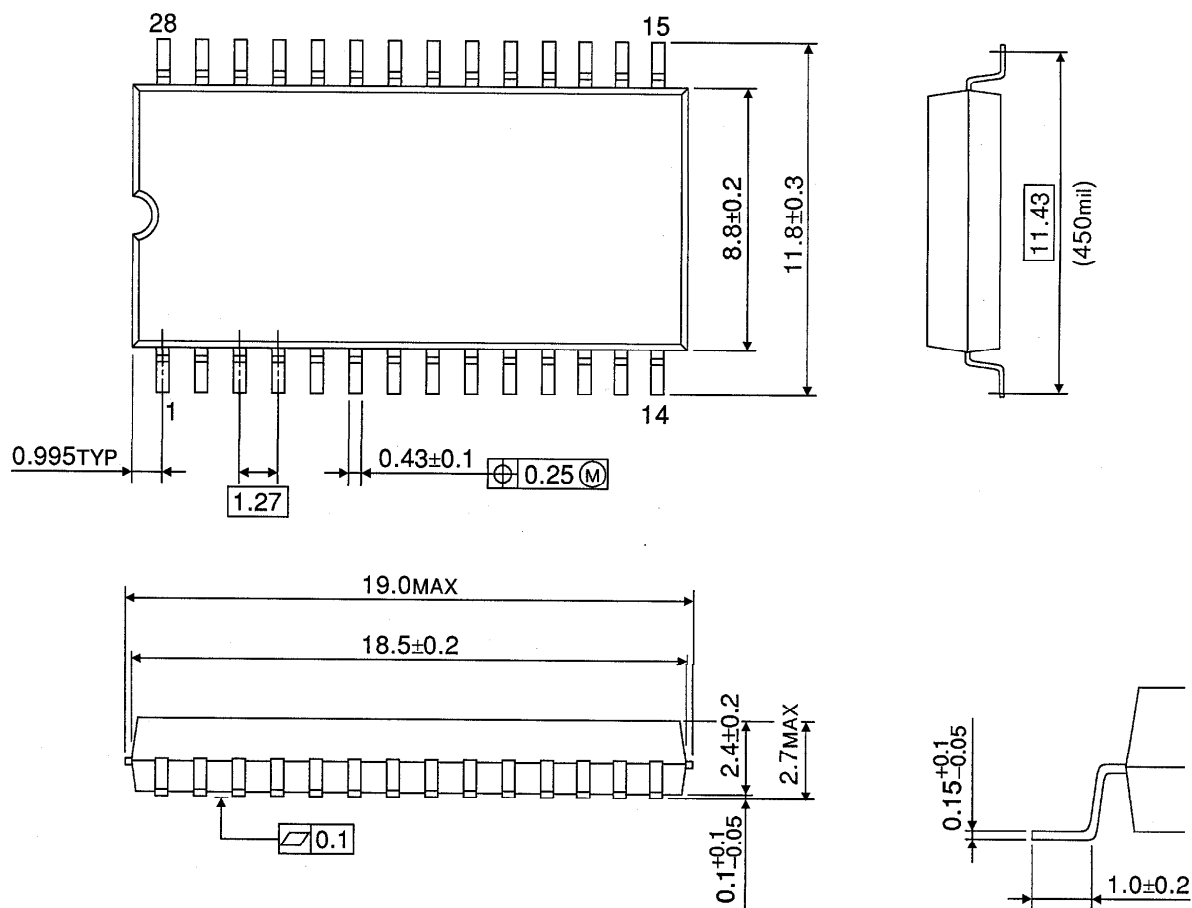
Units in mm



Weight: 4.42 g (typ)

PACKAGE DIMENSIONS (SOP28-P-450-1.27)

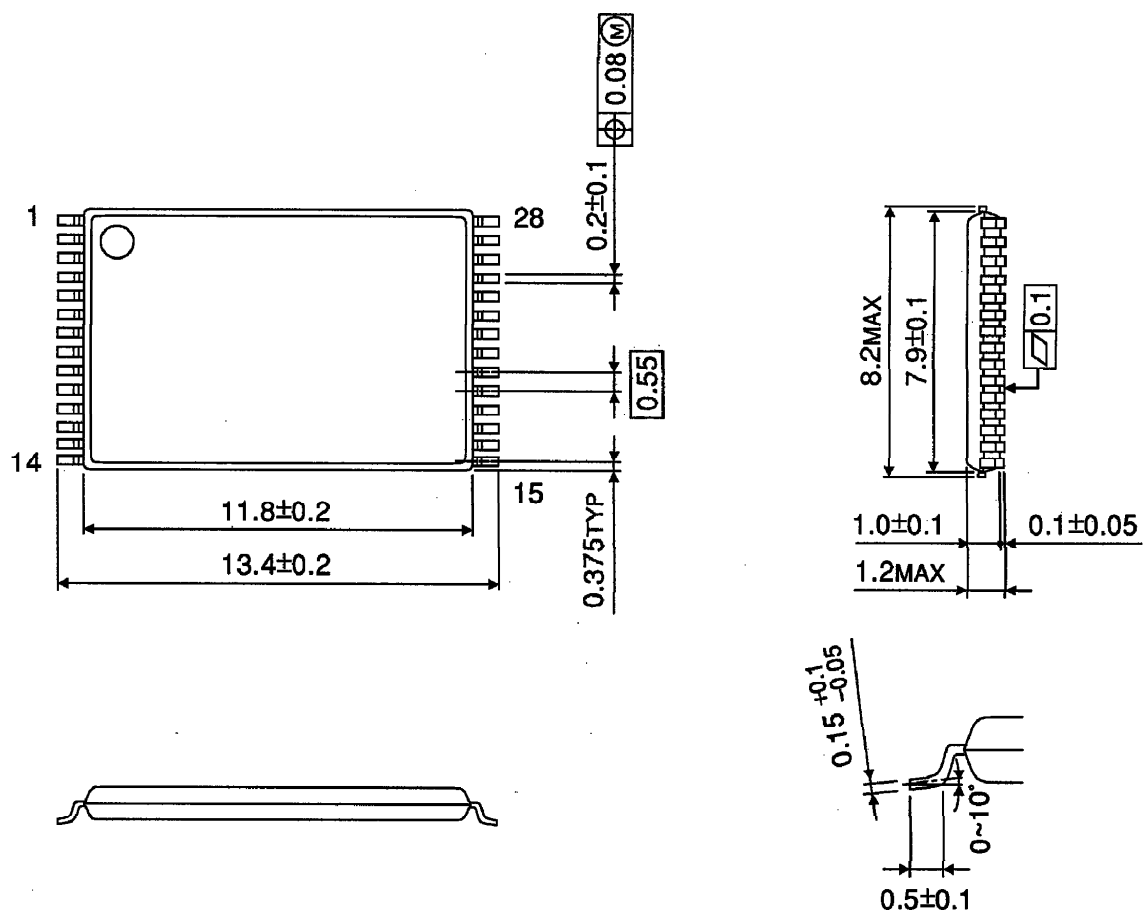
Units in mm



Weight: 0.79 g (typ)

PACKAGE DIMENSIONS (TSOP I 28-P-0.55)

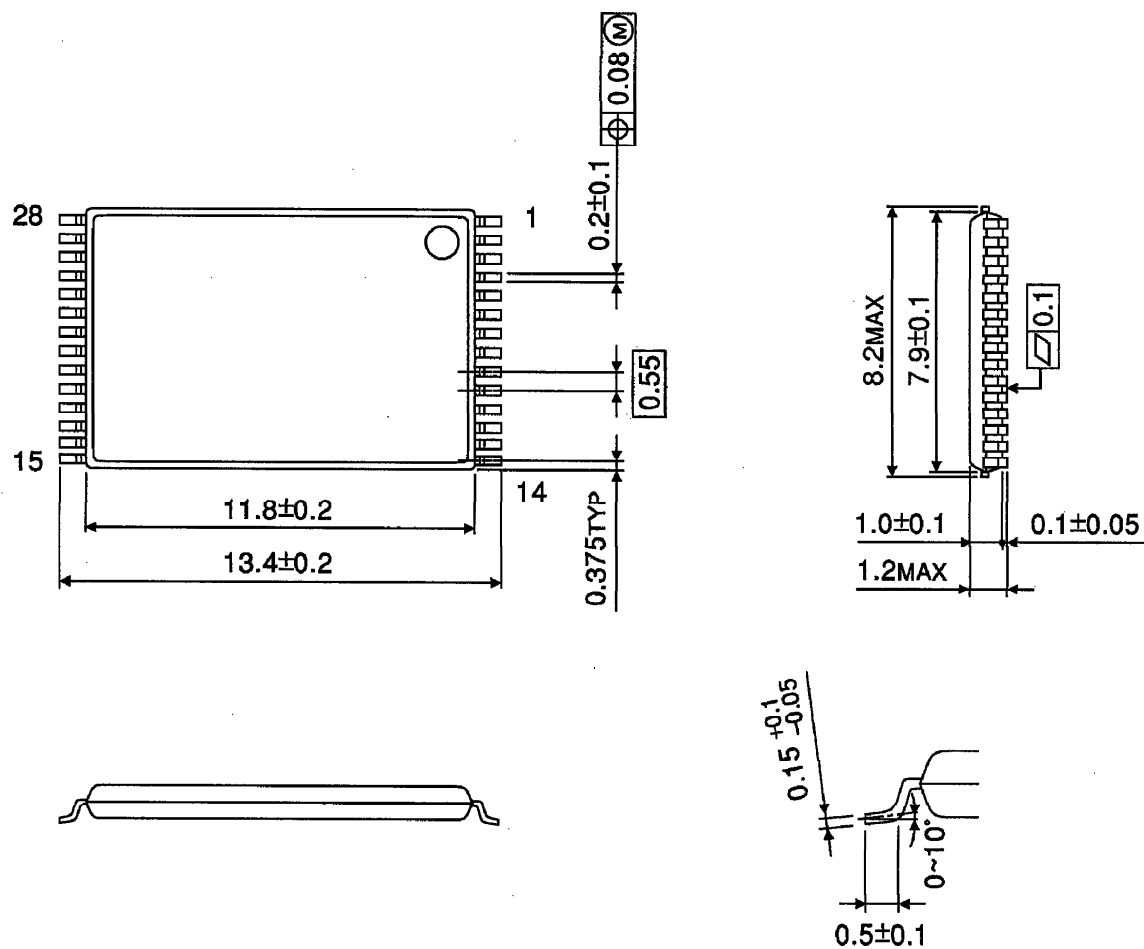
Units in mm



Weight: 0.22 g (typ)

PACKAGE DIMENSIONS (TSOP I 28-P-0.55A)

Units in mm



Weight: 0.22 g (typ)